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# ZXMN2F34FH

## 20V SOT23 N-channel enhancement mode MOSFET

### Summary

| $V_{(BR)DSS}$ | $R_{DS(on)}$ ( $\Omega$ ) | $I_D$ (A) |
|---------------|---------------------------|-----------|
| 20            | 0.060 @ $V_{GS} = 4.5V$   | 4.0       |
|               | 0.120 @ $V_{GS} = 2.5V$   | 2.9       |



### Description

This new generation Trench MOSFET from Zetex features low on-resistance achievable with low (2.5V) gate drive.

### Features

- Low on-resistance
- 2.5V gate drive capability
- SOT23 package

### Applications

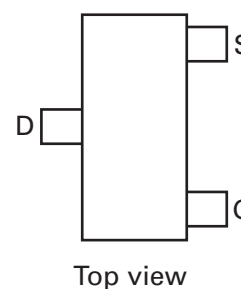
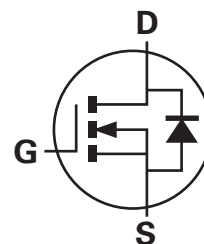
- Buck/Boost DC-DC Converters
- Motor Control
- LED Lighting

### Ordering information

| DEVICE       | Reel size (inches) | Tape width (mm) | Quantity per reel |
|--------------|--------------------|-----------------|-------------------|
| ZXMN2F34FHTA | 7                  | 8               | 3000              |

### Device marking

KNB



## ZXMN2F34FH

### Absolute maximum ratings

| Parameter  | Symbol         | Limit             | Unit                      |
|--|----------------|-------------------|---------------------------|
| Drain source voltage   | $V_{DSS}$      | 20                | V                         |
| Gate source voltage  | $V_{GS}$       | $\pm 12$          | V                         |
| Continuous Drain Current @ $V_{GS}=4.5$ ; $T_A=25^\circ\text{C}^{(b)}$<br>@ $V_{GS}=4.5$ ; $T_A=70^\circ\text{C}^{(b)}$<br>@ $V_{GS}=4.5$ ; $T_A=25^\circ\text{C}^{(a)}$ | $I_D$          | 4.0<br>3.3<br>3.4 | A<br>A<br>A               |
| Pulsed drain current <sup>(c)</sup>  | $I_{DM}$       | 18.6              | A                         |
| Continuous source current (body diode) <sup>(b)</sup>  | $I_S$          | 2.1               | A                         |
| Pulsed source current (body diode) <sup>(c)</sup>  | $I_{SM}$       | 18.6              | A                         |
| Power dissipation at $T_A=25^\circ\text{C}^{(a)}$<br>Linear derating factor  | $P_D$          | 0.95<br>7.6       | W<br>mW/ $^\circ\text{C}$ |
| Power dissipation at $T_A=25^\circ\text{C}^{(b)}$<br>Linear derating factor  | $P_D$          | 1.4<br>11         | W<br>mW/ $^\circ\text{C}$ |
| Operating and storage temperature range  | $T_j, T_{stg}$ | -55 to 150        | $^\circ\text{C}$          |

### Thermal resistance

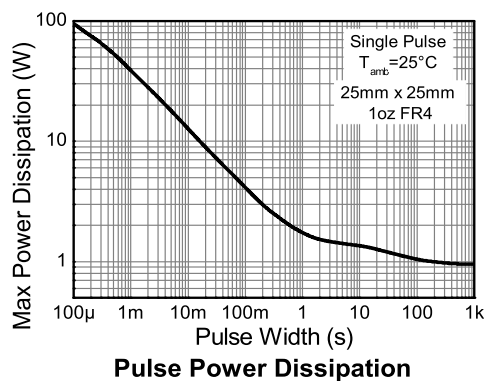
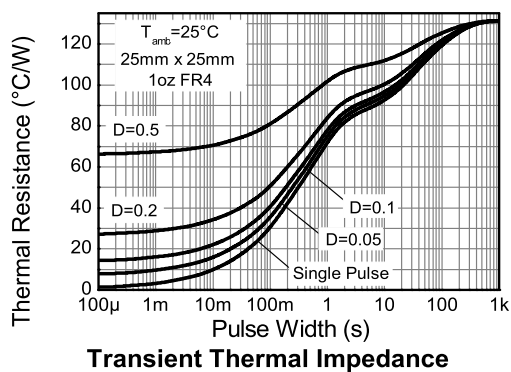
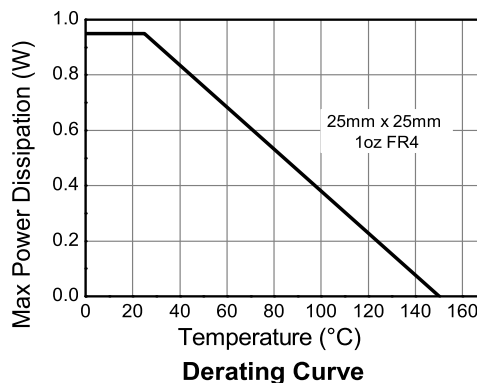
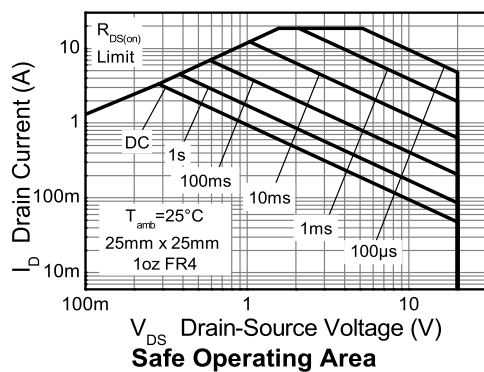
| Parameter                          | Symbol          | Limit | Unit               |
|------------------------------------|-----------------|-------|--------------------|
| Junction to ambient <sup>(a)</sup> | $R_{\theta JA}$ | 131   | $^\circ\text{C/W}$ |
| Junction to ambient <sup>(b)</sup> | $R_{\theta JA}$ | 89    | $^\circ\text{C/W}$ |
| Junction to lead <sup>(d)</sup>    | $R_{\theta JL}$ | 68    | $^\circ\text{C/W}$ |

#### NOTES:

- (a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.  
 (b) For a device surface mounted on FR4 PCB measured at  $t \leq 5$  sec.  
 (c) Repetitive rating - 25mm x 25mm FR4 PCB,  $D=0.02$ , pulse width 300 $\mu\text{s}$  - pulse width limited by maximum junction temperature.  
 (d) Thermal resistance from junction to solder-point (at end of drain lead).

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### Thermal characteristics



## ZXMN2F34FH

### Electrical characteristics (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

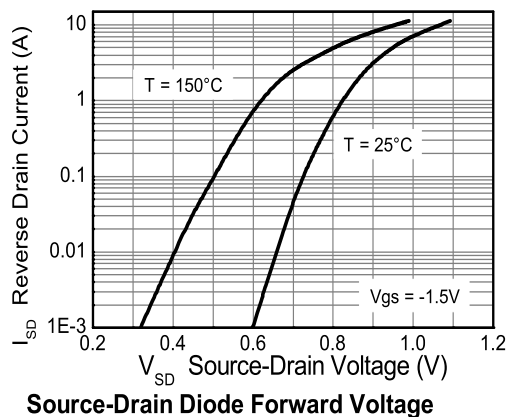
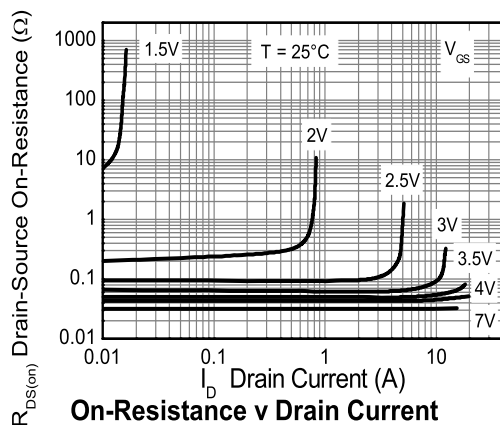
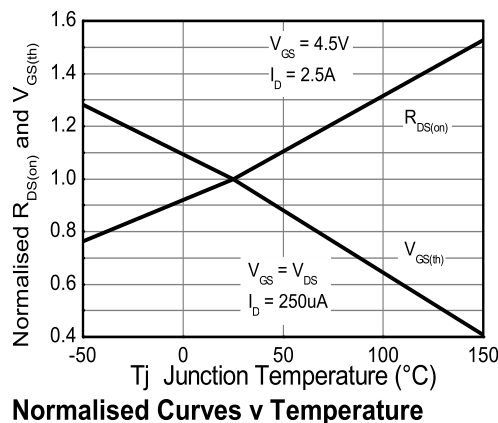
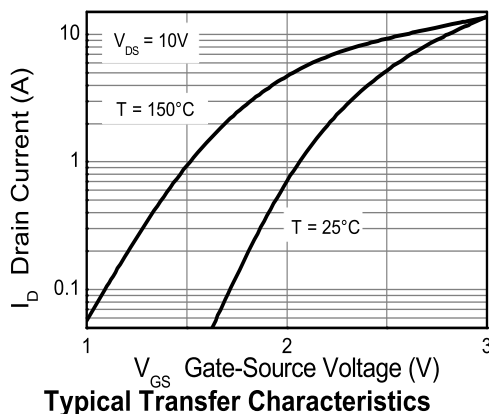
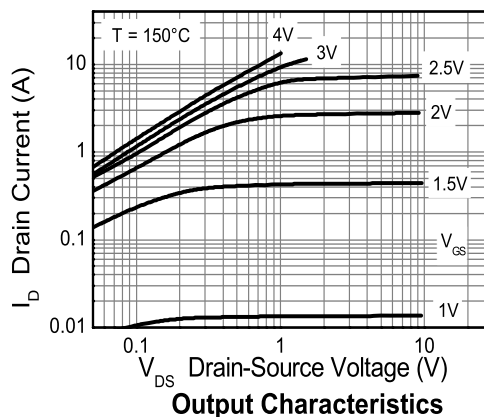
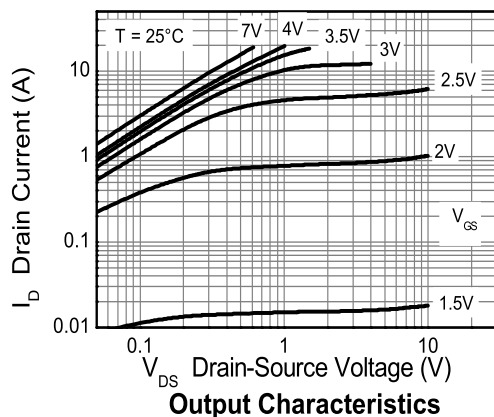
| Parameter                                   | Symbol               | Min. | Typ. | Max.           | Unit   | Conditions   |
|---|----------------------|------|------|----------------|--------|--|
| Static                                      |                      |      |      |                |        |  |
| Drain-Source Breakdown Voltage              | V <sub>(BR)DSS</sub> | 20   |      |                | V      | I <sub>D</sub> = 250μA, V <sub>GS</sub> =0V  |
| Zero Gate Voltage Drain Current             | I <sub>DSS</sub>     |      |      | 1              | μA     | V <sub>DS</sub> = 20V, V <sub>GS</sub> =0V   |
| Gate-Body Leakage                           | I <sub>GSS</sub>     |      |      | 100            | nA     | V <sub>GS</sub> =±12V, V <sub>DS</sub> =0V   |
| Gate-Source Threshold Voltage               | V <sub>GS(th)</sub>  | 0.5  | 0.8  | 1.5            | V      | I <sub>D</sub> = 250μA, V <sub>DS</sub> =V <sub>GS</sub>                                       |
| Static Drain-Source On-State Resistance (*) | R <sub>DS(on)</sub>  |      |      | 0.060<br>0.120 | Ω<br>Ω | V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 2.5A<br>V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 1.0A |
| Forward Transconductance(*) (†)             | g <sub>fs</sub>      |      | 7.5  |                | S      | V <sub>DS</sub> = 10V, I <sub>D</sub> = 2.5A   |
| Dynamic (†)                                 |                      |      |      |                |        |  |
| Input Capacitance                           | C <sub>iss</sub>     |      | 277  |                | pF     | V <sub>DS</sub> = 10V, V <sub>GS</sub> =0V<br>f=1MHz   |
| Output Capacitance                          | C <sub>oss</sub>     |      | 65   |                | pF     |  |
| Reverse Transfer Capacitance                | C <sub>rss</sub>     |      | 35   |                | pF     |  |
| Switching (‡)(†)                            |                      |      |      |                |        |  |
| Turn-On-Delay Time                          | t <sub>d(on)</sub>   |      | 2.65 |                | ns     | V <sub>DD</sub> = 10V, V <sub>GS</sub> = 4.5V<br>I <sub>D</sub> = 1A<br>R <sub>G</sub> ≈ 6.0Ω  |
| Rise Time                                   | t <sub>r</sub>       |      | 4.2  |                | ns     |  |
| Turn-Off Delay Time                         | t <sub>d(off)</sub>  |      | 9.9  |                | ns     |  |
| Fall Time                                   | t <sub>f</sub>       |      | 5.1  |                | ns     |  |
| Total Gate Charge                           | Q <sub>g</sub>       |      | 2.8  |                | nC     | V <sub>DS</sub> = 10V, V <sub>GS</sub> = 4.5V<br>I <sub>D</sub> = 2.5A                         |
| Gate-Source Charge                          | Q <sub>gs</sub>      |      | 0.61 |                | nC     |  |
| Gate Drain Charge                           | Q <sub>gd</sub>      |      | 0.63 |                | nC     |  |
| Source-drain diode                          |                      |      |      |                |        |  |
| Diode Forward Voltage(*)                    | V <sub>SD</sub>      |      | 0.73 | 1.2            | V      | I <sub>S</sub> = 1.25A, V <sub>GS</sub> =0V  |
| Reverse recovery time(†)                    | t <sub>rr</sub>      |      | 6.5  |                | ns     | T <sub>J</sub> =25°C, I <sub>F</sub> =1.65A<br>di/dt=100A/μs                                   |
| Reverse recovery charge(†)                  | Q <sub>rr</sub>      |      | 1.4  |                | nC     |  |

#### NOTES:

- (\*) Measured under pulsed conditions. Pulse width  $\leq 300\mu\text{s}$ ; duty cycle  $\leq 2\%$ .  
 (†) For design aid only, not subject to production testing.  
 (‡) Switching characteristics are independent of operating junction temperature.

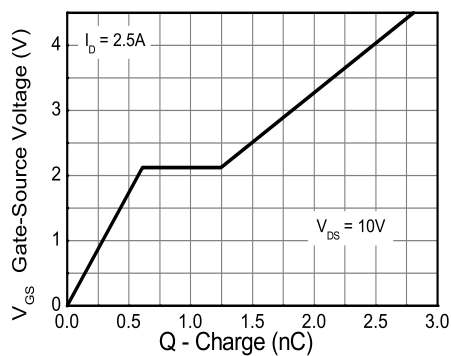
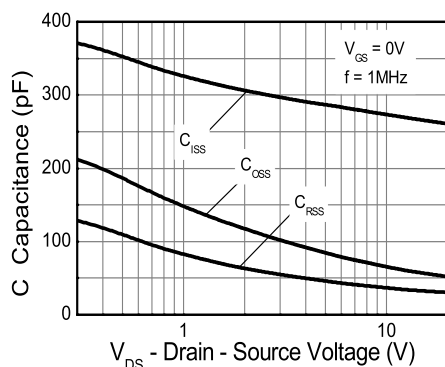
## ZXMN2F34FH

### Typical characteristics

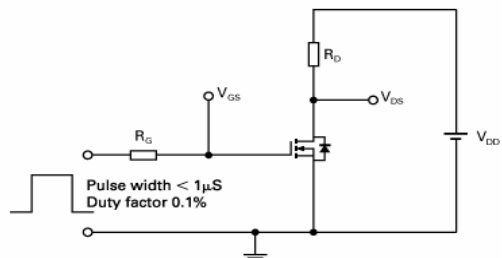
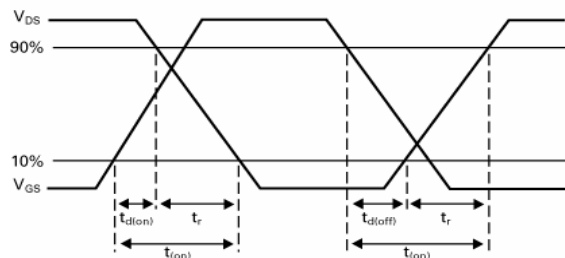
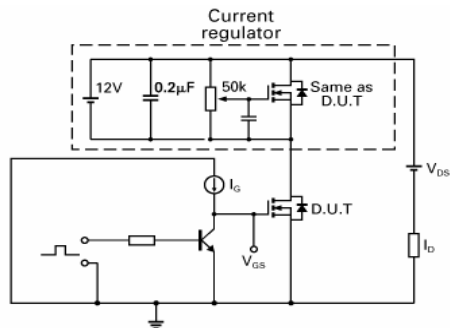
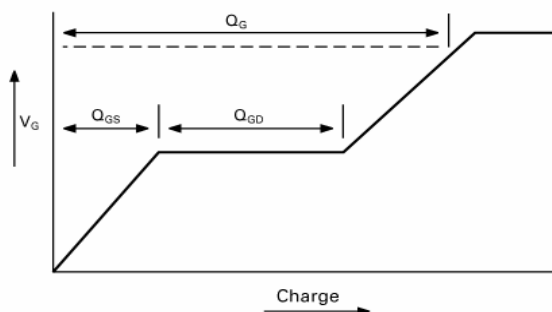


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### Typical characteristics

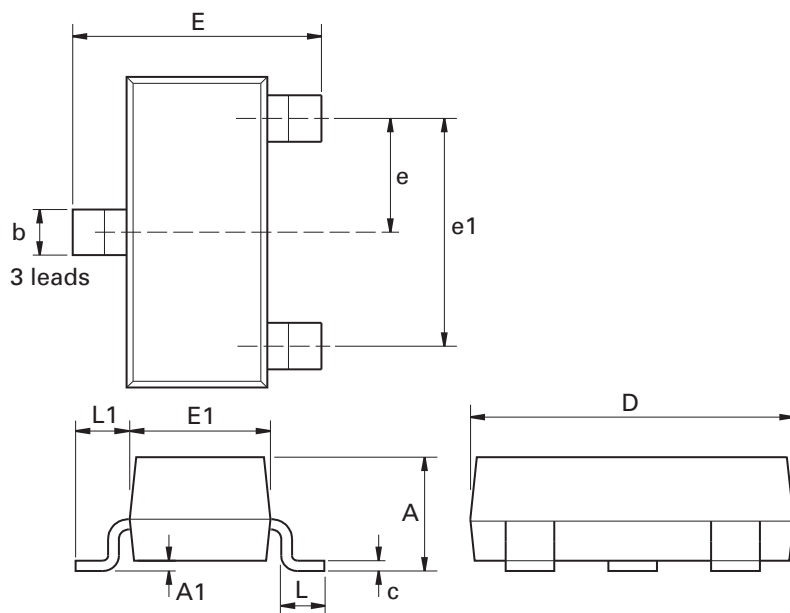


### Test circuits



## ZXMN2F34FH

### Package outline - SOT23



| Dim. | Millimeters |      | Inches    |       | Dim. | Millimeters |      | Inches    |        |
|------|-------------|------|-----------|-------|------|-------------|------|-----------|--------|
|      | Min.        | Max. | Min.      | Max.  |      | Min.        | Max. | Min.      | Max.   |
| A    | -           | 1.12 | -         | 0.044 | e1   | 1.90 NOM    |      | 0.075 NOM |        |
| A1   | 0.01        | 0.10 | 0.0004    | 0.004 | E    | 2.10        | 2.64 | 0.083     | 0.104  |
| b    | 0.30        | 0.50 | 0.012     | 0.020 | E1   | 1.20        | 1.40 | 0.047     | 0.055  |
| c    | 0.085       | 0.20 | 0.003     | 0.008 | L    | 0.25        | 0.60 | 0.0098    | 0.0236 |
| D    | 2.80        | 3.04 | 0.110     | 0.120 | L1   | 0.45        | 0.62 | 0.018     | 0.024  |
| e    | 0.95 NOM    |      | 0.037 NOM |       | -    | -           | -    | -         | -      |

**Note:** Controlling dimensions are in millimeters. Approximate dimensions are provided in inches



# ZXMN2F34FH

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### Product status key:

|                                   |  |
|-----------------------------------|--|
| "Preview"                         | Future device intended for production at some point. Samples may be available  |
| "Active"                          | Product status recommended for new designs                                     |
| "Last time buy (LTB)"             | Device will be discontinued and last time buy period and delivery is in effect |
| "Not recommended for new designs" | Device is still in production to support existing designs and production       |
| "Obsolete"                        | Production has been discontinued   |

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|                       |   |
|-----------------------|---|
| "Draft version"       | This term denotes a very early datasheet version and contains highly provisional information, which may change in any manner without notice.  |
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